

# PSMN4R2-60PL

N-channel 60 V, 3.9 mΩ logic level MOSFET in SOT78
5 February 2013 Product data sheet

## 1. General description

Logic level N-channel MOSFET in SOT78 using TrenchMOS technology. Product design and manufacture has been optimized for use in battery operated power tools.

#### 2. Features and benefits

- High efficiency due to low switching & conduction losses
- Robust construction for demanding applications
- Logic level gate

## 3. Applications

- Battery-powered tools
- Load switching
- Motor control
- Uninterruptible power supplies

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	-	130	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	263	W
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11		-	3.17	3.9	mΩ
Dynamic chara	acteristics						
Q <sub>G(tot)</sub>	total gate charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 48 V;		-	151	-	nC
$Q_{GD}$	gate-drain charge	Fig. 13; Fig. 14		-	27	-	nC
Avalanche rug	gedness						
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 130 A; $V_{sup} \le$ 60 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3		-	-	283	mJ

<sup>[1]</sup> Continuous current is limited by package.



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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain	<del>                                     </del>	
3	S	source	TO-220AB (SOT78)	mbb076 S

## 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PSMN4R2-60PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN4R2-60PL	PSMN4R2-60PL

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	60	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	130	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>		-	124	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4		-	701	А

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Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	263	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	130	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	701	Α
Avalanche	ruggedness		1			
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 130 A; $V_{sup} \le$ 60 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3		-	283	mJ

#### [1] Continuous current is limited by package.

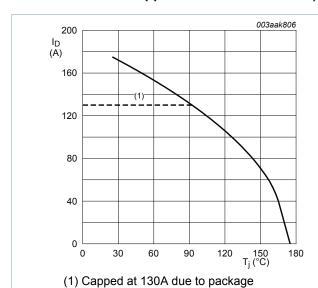


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10V$$

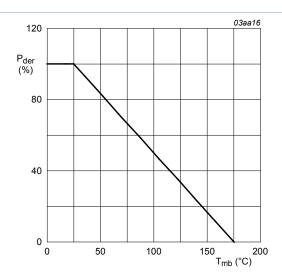


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \,\%$$

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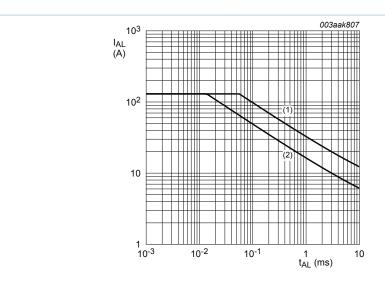
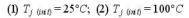


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time



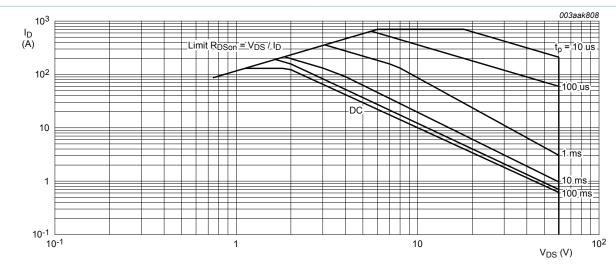


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

### 9. Thermal characteristics

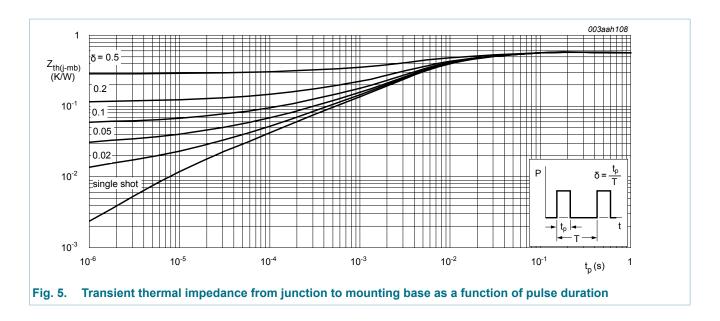
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	0.49	0.57	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

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## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	60	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	54	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	V
I <sub>DSS</sub> drain leakage currer	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.06	1	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	3.6	4.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	3.17	3.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; <u>Fig. 12</u> ; <u>Fig. 11</u>	-	-	8.6	mΩ
$R_G$	gate resistance	f = 1 MHz	0.35	0.7	1.4	Ω

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics		l l			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V; Fig. 13; Fig. 14	-	151	-	nC
		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 5 V; Fig. 13; Fig. 14	-	72	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V;	-	20	-	nC
$Q_{GD}$	gate-drain charge	Fig. 13; Fig. 14	-	27	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 15$	-	8533	-	pF
C <sub>oss</sub>	output capacitance		-	703	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	357	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 45 V; $R_{L}$ = 1.8 $\Omega$ ; $V_{GS}$ = 5 V;	-	47	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	97	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	84	-	ns
t <sub>f</sub>	fall time		-	73	-	ns
Source-dra	in diode		l l			
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	40	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V	-	59	-	nC

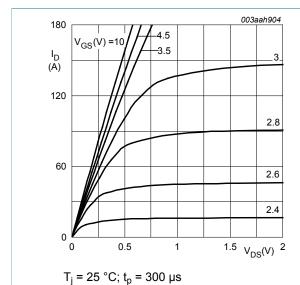


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

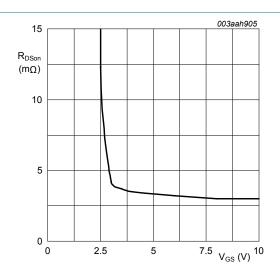


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

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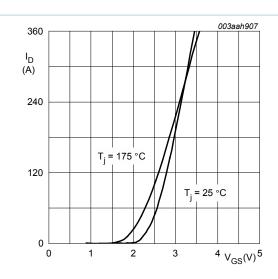


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



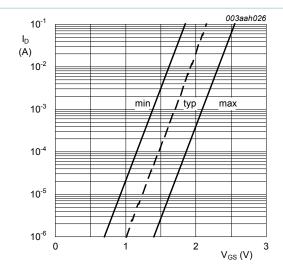


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C;  $V_{DS} = 5V$ 

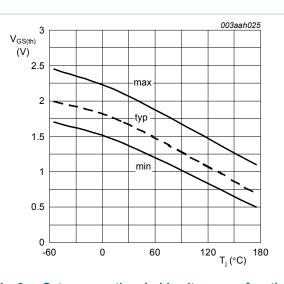
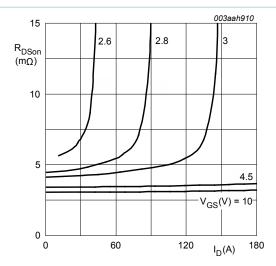


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$



 $T_i$  = 25 °C;  $t_p$  = 300  $\mu$ s

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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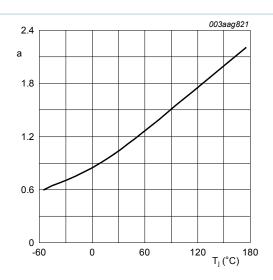


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$\mathbf{a} = \frac{R_{DSon}}{R_{DSon(25~\mathrm{C})}}$$

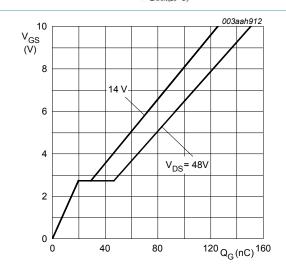


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; \ I_D = 25A$$

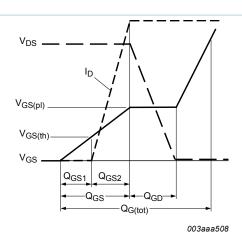


Fig. 13. Gate charge waveform definitions

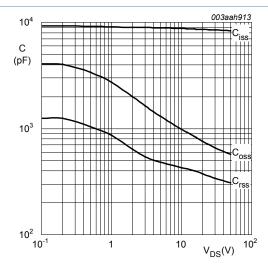


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$$

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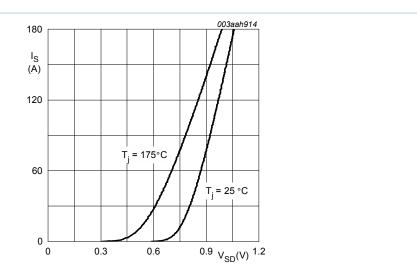
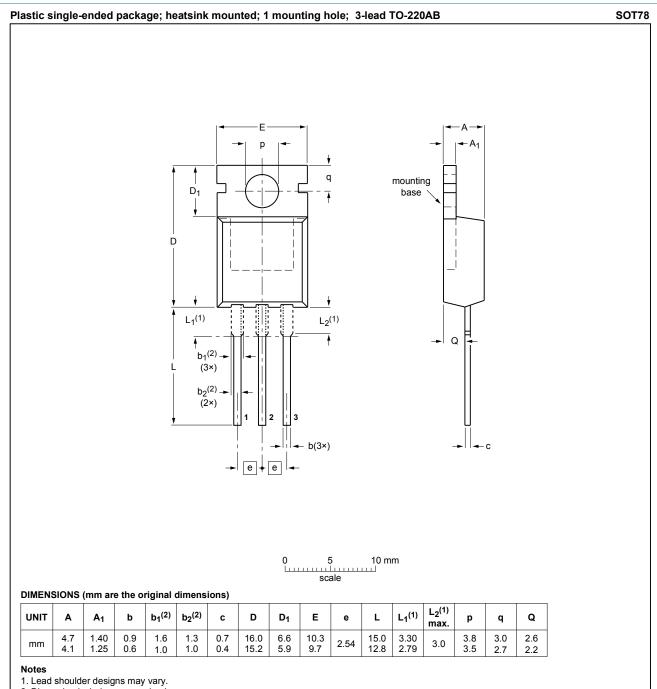


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

## 11. Package outline



2. Dimension includes excess dambar.

OUTLINE	REFERENCES		REFERENCES EUROF		REFERENCES		EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE		
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13		

Fig. 17. Package outline TO-220AB (SOT78)

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